Supplementary file

Plasma-free anisotropic selective-area etching of β-Ga_2O_3 using forming gas under atmospheric pressure

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Supplementary file

1. Window designs

Square, circular, radial-line, striped window patterns utilized in the experiments are shown in Figure S1 for easy understanding.

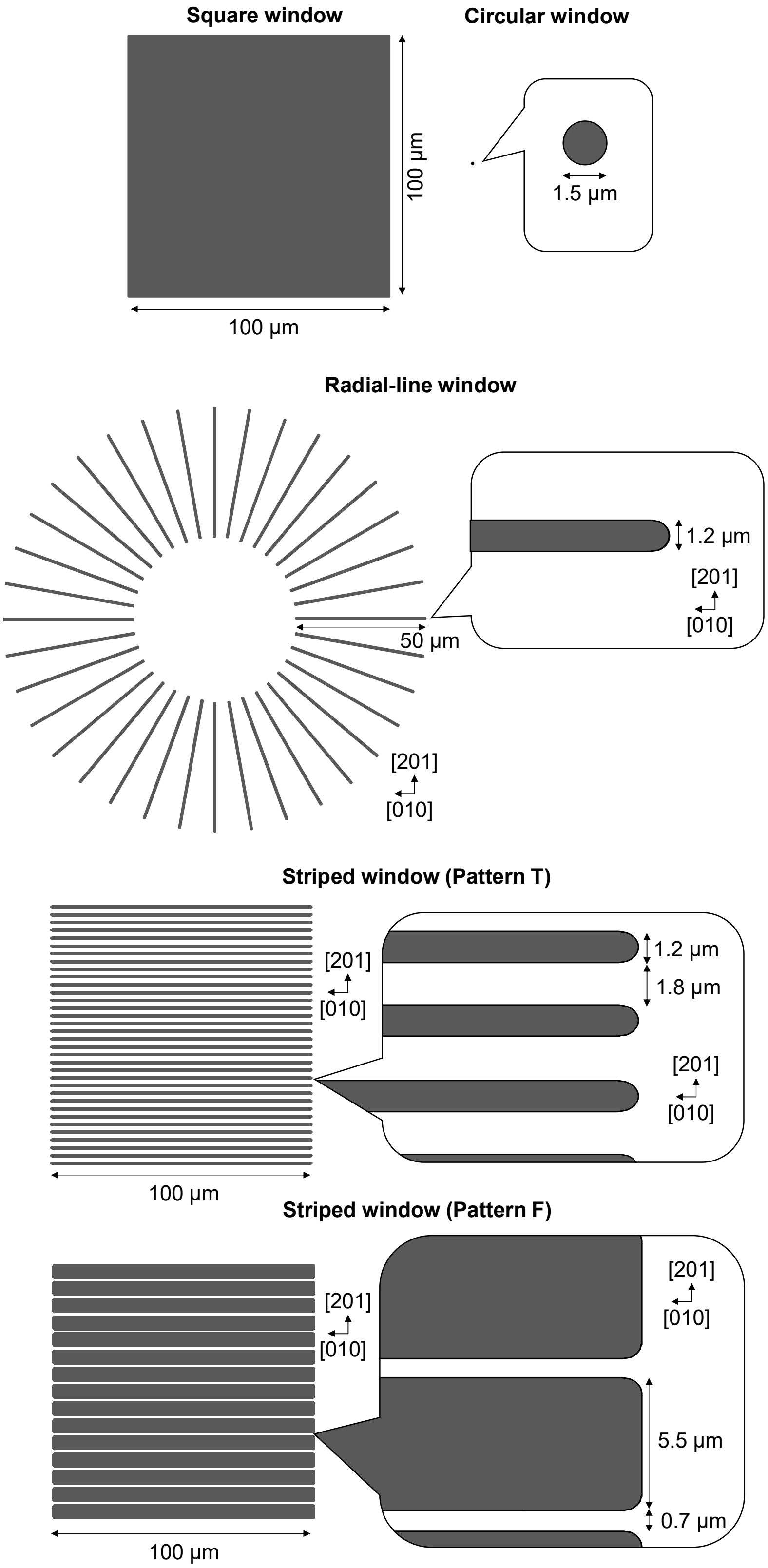

Figure S1. Designs of the window patterns used in the etching experiments. For further details, please refer to the original paper. Note that the ends of the line patterns are curved due to the finite size of the laser spot.